



### General Description

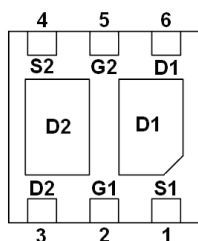
AFP3911W, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

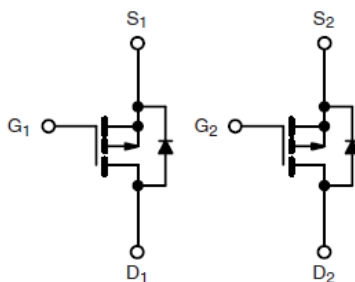
### Features

- -30V/-3A,  $R_{DS(ON)}=68m\Omega@V_{GS}=-10V$
- -30V/-2A,  $R_{DS(ON)}=88m\Omega@V_{GS}=-4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN2X2-6L package design

### Pin Description ( DFN2X2-6L )



BOTTOM VIEW



TOP VIEW

### Application

- Smart Phones, Tablet PCs, Mobile Computing :
  - Battery Switches
  - Load Switches
  - Power Management

### Pin Define

Pin	Symbol	Description
1	S1	Source1
2	G1	Gate1
3	D2	Drain2
4	S2	Source2
5	G2	Gate2
6	D1	Drain1

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP3911WFN226RG	391YW	DFN2X2-6L	Tape & Reel	4000 EA

- ※ 391 parts code
- ※ Y year code
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFP3911WFN226RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



**Absolute Maximum Ratings**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-30	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-4.3
		T <sub>A</sub> =70°C	-3.4
Pulsed Drain Current	I <sub>DM</sub>	-28	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>C</sub> =25°C	7.8
		T <sub>C</sub> =70°C	5.0
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

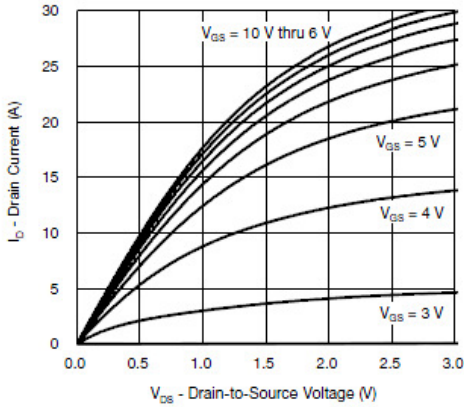
**Electrical Characteristics**

(T<sub>A</sub>=25°C Unless otherwise noted)

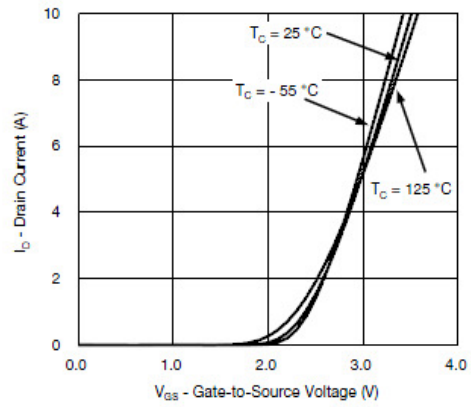
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.0		-2.0	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V			-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			-30	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> =-10V	-10			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		55	68	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A		75	88	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-3A		8		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3A, V <sub>GS</sub> =0V		-0.75	-1.3	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V I <sub>D</sub> ≡-4.0A		4.2	7.2	nC
Gate-Source Charge	Q <sub>gs</sub>			1.3		
Gate-Drain Charge	Q <sub>gd</sub>			1.6		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V f=1MHz		450		pF
Output Capacitance	C <sub>oss</sub>			56		
Reverse Transfer Capacitance	C <sub>rss</sub>			46		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, R <sub>L</sub> =5Ω I <sub>D</sub> ≡-3A, V <sub>GEN</sub> =-10V R <sub>G</sub> =1Ω		10	20	ns
	t <sub>r</sub>			5	10	
Turn-Off Time	t <sub>d(off)</sub>			20	40	
	t <sub>f</sub>			5	10	



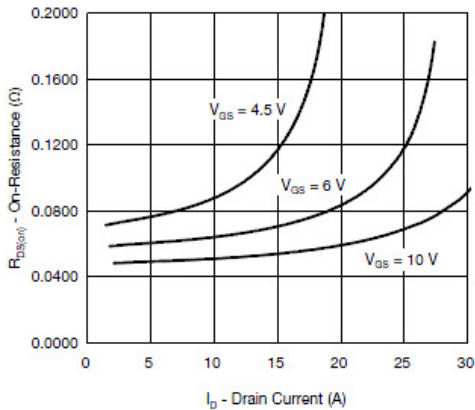
## Typical Characteristics



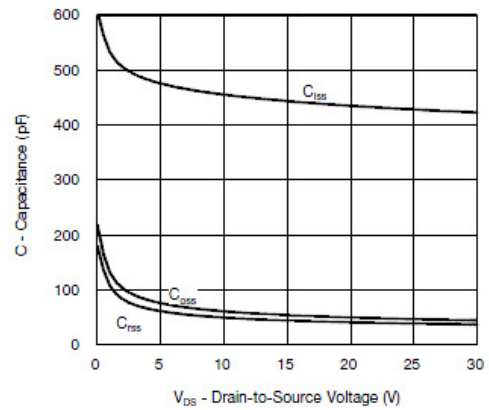
Output Characteristics



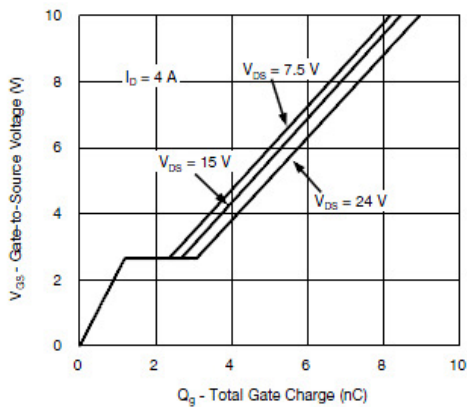
Transfer Characteristics



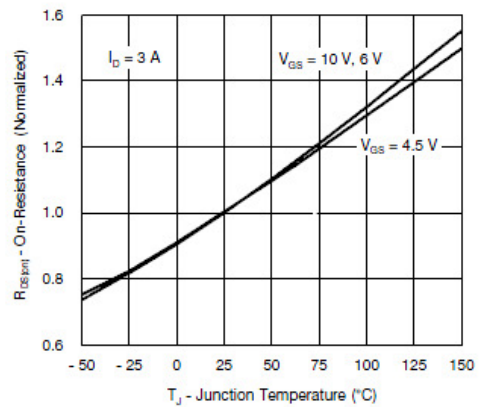
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



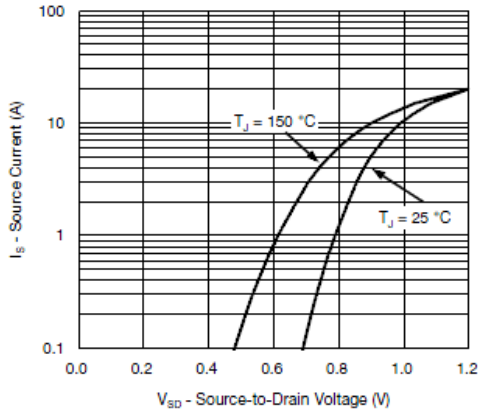
Gate Charge



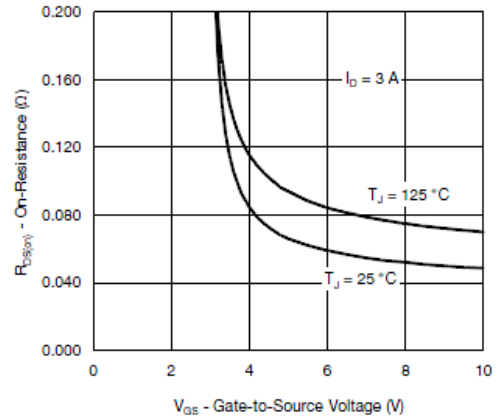
On-Resistance vs. Junction Temperature



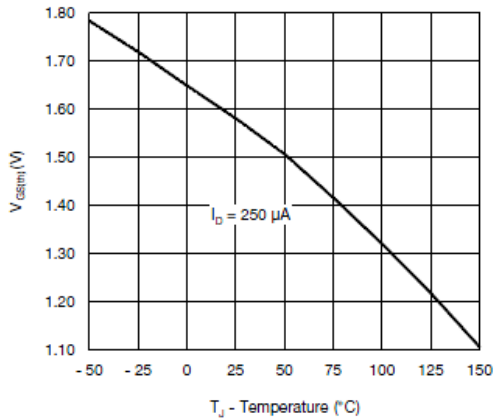
## Typical Characteristics



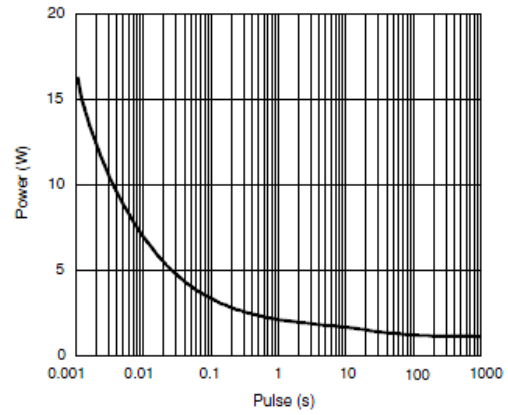
Source-Drain Diode Forward Voltage



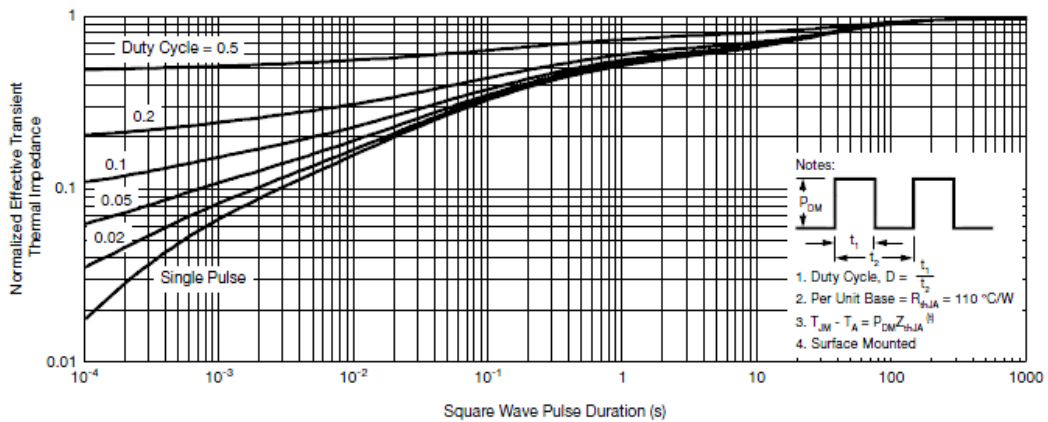
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

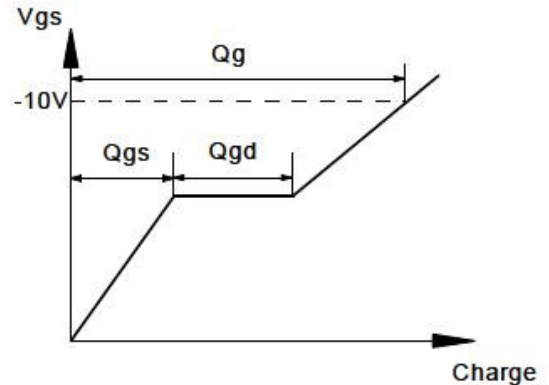
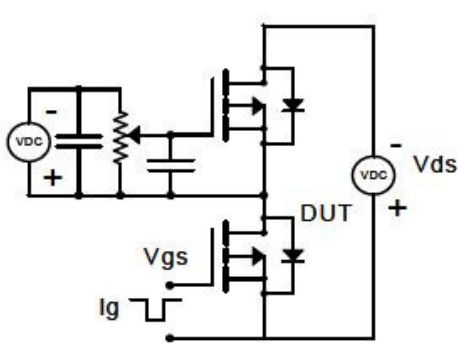


Normalized Thermal Transient Impedance, Junction-to-Ambient

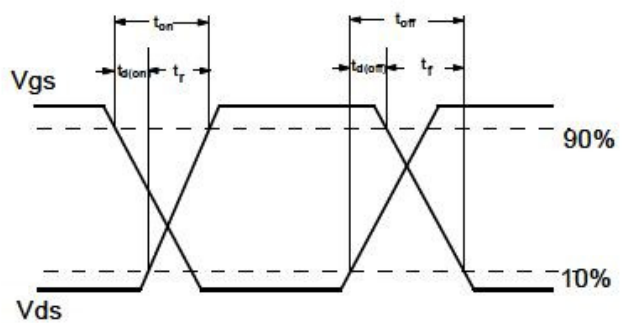
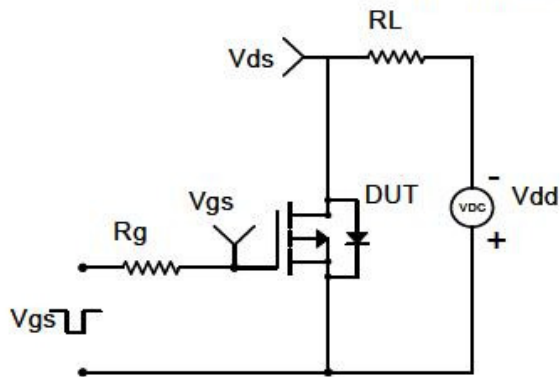


**Typical Characteristics**

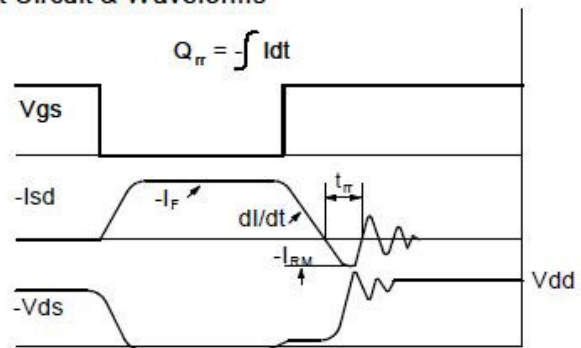
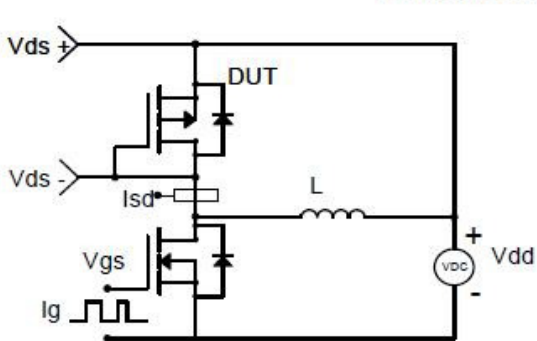
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

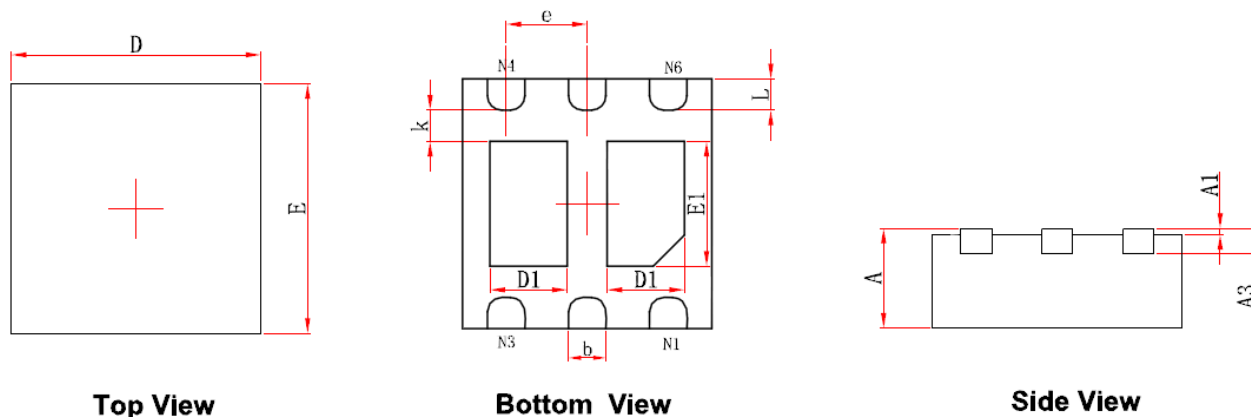


Diode Recovery Test Circuit & Waveforms





**Package Information ( DFN2X2-6L )**



**Top View**

**Bottom View**

**Side View**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700/0.800	0.800/0.900	0.028/0.031	0.031/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.520	0.720	0.020	0.028
E1	0.900	1.100	0.035	0.043
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013

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2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)  
Tel : 886 2) 2651 3928  
Fax : 886 2) 2786 8483  
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